

The documentation and process conversion measures necessary to comply with this revision shall be completed by 22 June 2016.

INCH-POUND

MIL-PRF-19500/502H
 22 March 2016
 SUPERSEDING
 MIL-PRF-19500/502G
 28 February 2014

PERFORMANCE SPECIFICATION SHEET

TRANSISTOR, DARLINGTON, NPN, SILICON, POWER,
 ENCAPSULATED (THROUGH-HOLE MOUNT PACKAGE)
 TYPES 2N6058 AND 2N6059, QUALITY LEVELS JAN, JANTX, AND JANTXV

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for NPN silicon power Darlington transistors. Three levels of product assurance are (JAN, JANTX, and JANTXV) provided for each encapsulated device.

1.2 Package outlines. The device package outlines are as follows: TO-204AA (similar to TO-3) in accordance with [figure 1](#) for all encapsulated device types.

1.3 Maximum ratings. Unless otherwise specified, $T_c = +25^\circ\text{C}$.

Types	P_T		V_{CBO}	V_{CEO}	V_{EBO}	I_c	I_B	T_J and T_{STG}
	$T_c = +25^\circ\text{C}$ (1)	$T_c = +100^\circ\text{C}$						
	<u>W</u>	<u>W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>°C</u>
2N6058	150	75	80	80	5	12	0.2	-55 to +175
2N6059	150	75	100	100	5	12	0.2	-55 to +175

(1) Derate linearly at 1.00 W/°C above $T_c > +25^\circ\text{C}$.

Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to semiconductor@dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil>.



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1.4 Primary electrical characteristics. Unless otherwise specified, $T_c = +25^\circ\text{C}$.

Limit	h_{FE2} (1) $V_{CE} = 3 \text{ V dc}$ $I_C = 6 \text{ A dc}$	h_{FE3} (1) $V_{CE} = 3 \text{ V dc}$ $I_C = 12 \text{ A dc}$	h_{fe} $V_{CE} = 3 \text{ V dc}$ $I_C = 5 \text{ A dc}$ $f = 1 \text{ kHz}$	$ h_{fe} $ $V_{CE} = 3 \text{ V dc}$ $I_C = 5 \text{ A dc}$ $f = 1 \text{ MHz}$	C_{obo} $100 \text{ kHz} \leq f \leq 1 \text{ MHz}$ $V_{CB} = 10 \text{ V dc}$ $I_E = 0$	$R_{\theta JC}$
Minimum	1,000	150	1,000	10	μF	$^\circ\text{C/W}$
Maximum	18,000			250	300	1.0

Limit	$V_{BE(sat)}$ (1) $I_C = 12 \text{ A dc}$ $I_B = 120 \text{ mA dc}$	$V_{CE(sat)1}$ (1) $I_C = 12 \text{ A dc}$ $I_B = 120 \text{ mA dc}$	$V_{CE(sat)2}$ (1) $I_C = 6 \text{ A dc}$ $I_B = 24 \text{ mA dc}$	Pulse response (2)	
				t_{on}	t_{off}
	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>μs</u>	<u>μs</u>
Minimum	4.0	3.0	2.0	2	10
Maximum					

(1) Pulsed (see 4.5.1).

(2) See figure 2 for pulse response circuits.

1.5 Part or Identifying Number (PIN). The PIN is in accordance with MIL-PRF-19500, and as specified herein. See 6.4 for PIN construction example and 6.5 for a list of available PINs.

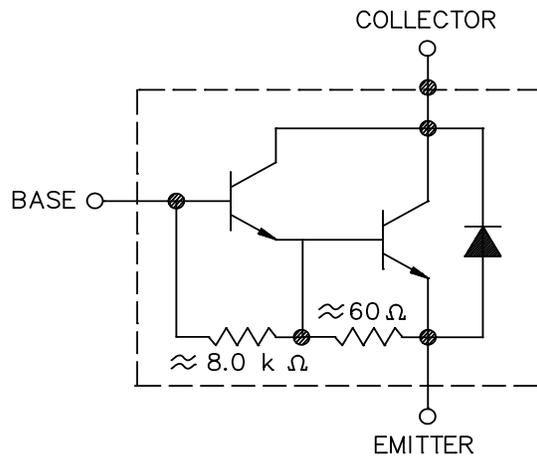
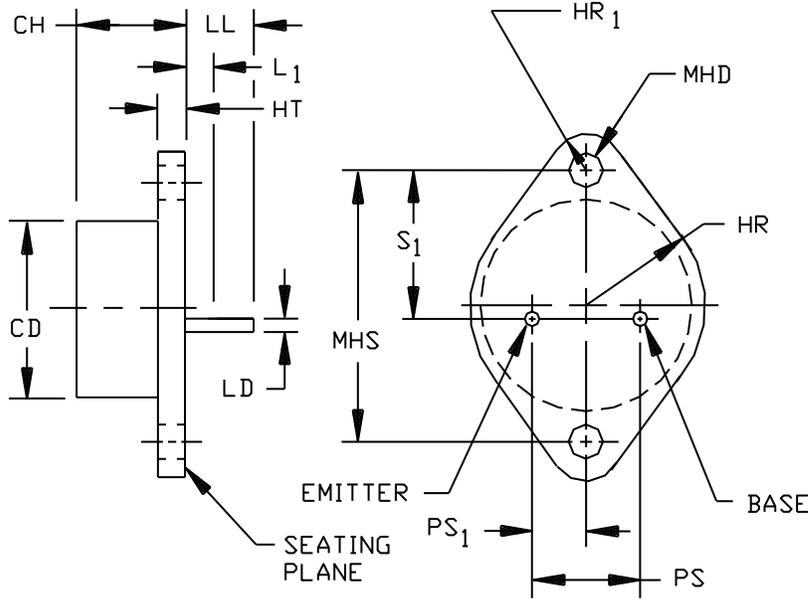
1.5.1 JAN certification mark and quality level for encapsulated devices. The quality level designators for encapsulated devices that are applicable for this specification sheet from the lowest to the highest level are as follows: "JAN", "JANTX", and "JANTXV".

1.5.2 Device type. The designation system for the device types of transistors covered by this specification sheet are as follows.

1.5.2.1 First number and first letter symbols. The transistors of this specification sheet use the first number and letter symbols "2N".

1.5.2.2 Second number symbols. The second number symbols for the transistors covered by this specification sheet are as follows: "6058" and "6059".

1.5.3 Lead finish. The lead finishes applicable to this specification sheet are listed on QPDSIS-19500.



SCHEMATIC CIRCUIT

FIGURE 1. Physical dimensions and schematic circuit (TO-204AA, similar to TO-3).

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Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD		.875		22.23	
CH	.250	.328	6.35	8.33	
HR	.495	.525	12.57	13.34	
HR ₁	.131	.188	3.33	4.78	3
HT	.060	.135	1.52	3.43	
LD	.038	.043	0.97	1.09	4, 5
LL	.312	.500	7.92	12.7	4
L ₁		.050		1.27	4, 5
MHD	.151	.161	3.84	4.09	6
MHS	1.177	1.197	29.90	30.40	
PS	.420	.440	10.67	11.18	7, 8
PS ₁	.205	.225	5.21	5.72	7, 4, 8
S ₁	.655	.675	16.64	17.15	7

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Body contour is optional within zone defined by dimension CD.
3. At both ends.
4. Both terminals.
5. Dimension LD applies between dimension L₁ and LL. Lead diameter shall not exceed twice dimension LD within dimension L₁. Diameter is uncontrolled in dimension L₁.
6. Two holes.
7. These dimensions shall be measured at points .050 inch (1.27 mm) to .055 inch (1.40 mm) below the seating plane. When gauge is not used, measurement shall be made at seating plane.
8. The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
9. The collector shall be electrically connected to the case.
10. In accordance with ASME Y14.5M, diameters are equivalent to ϕ symbology.

FIGURE 1. Physical dimensions and schematic circuit (TO-204AA, similar to TO-3) - Continued.

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

[MIL-PRF-19500](#) - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

[MIL-STD-750](#) - Test Methods for Semiconductor Devices.

(Copies of these documents are available online at <http://quicksearch.dla.mil/>).

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in [MIL-PRF-19500](#) and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see [4.2](#) and [6.3](#)).

3.3 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein shall be as specified in [MIL-PRF-19500](#) and as follows:

I_M	-	The measurement current applied to forward bias the junction for measurement of V_{BE} .
I_H	-	The collector current applied to the device under test during the heating period.
t_H	-	The duration of the applied heating power pulse.
t_{sw}	-	Sample window time during which final V_{BE} measurement is made.

3.4 Interface requirements and physical dimensions. The interface requirements and physical dimensions shall be as specified in [MIL-PRF-19500](#) and on [figure 1](#) (TO-204AA, similar to TO-3) herein.

3.4.1 Lead finish. The lead finish shall be solderable in accordance with [MIL-STD-750](#), [MIL-PRF-19500](#), and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see [6.2](#)).

3.4.2 Polarity. The polarity of the device types shall be as shown on [figure 1](#). The collector shall be electrically connected to the case.

3.5 Marking. Marking shall be in accordance with [MIL-PRF-19500](#).

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in [1.3](#), [1.4](#), and [table I](#) herein.

3.7 Electrical test requirements. The electrical test requirements shall be as specified in [table I](#).

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see [4.3](#)).
- c. Conformance inspection (see [4.4](#) and [tables I and II](#)).

4.2 Qualification inspection. Qualification inspection shall be in accordance with [MIL-PRF-19500](#), and as specified herein.

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of [table II](#) tests, the tests specified in [table II](#) herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

4.3 Screening (JANTX and JANTXV levels only). Screening shall be in accordance with table E-IV of [MIL-PRF-19500](#), and as specified herein. The following measurements shall be made in accordance with [table I](#) herein. Devices that exceed the limits of [table I](#) herein shall not be acceptable.

Screen (see table E-IV of MIL-PRF-19500)	Measurement
	JANTX and JANTXV levels only
3c (1)	Thermal impedance, see 4.3.1
9	I_{CEX1} .
11	I_{CEX1} , h_{FE2} ; ΔI_{CEX1} = 100 percent of initial value or 2 μ A dc, whichever is greater.
12	See 4.3.2.
13	See table I , subgroup 2 herein. ΔI_{CEX1} = 100 percent of initial value or 2 μ A dc, whichever is greater. Δh_{FE2} = \pm 40 percent of initial value.

(1) This test shall be performed anytime after temperature cycling, screen 3a, and does not need to be repeated in screening requirements.

4.3.1 Thermal impedance. The thermal impedance measurements shall be performed in accordance with test method 3131 of [MIL-STD-750](#) using the guidelines in that test method for determining I_M , I_H , t_H , t_{SW} , (and V_H where appropriate). The thermal impedance limit used in screen 3c and [table I](#), subgroup 2 herein shall be set statistically by the supplier. See [table II](#), subgroup 4 herein.

4.3.2 Power burn-in conditions. The power burn-in conditions shall be as follows: $T_J = +162.5^\circ\text{C} \pm 12.5^\circ\text{C}$; $V_{CE} \geq 10 \text{ V dc}$, $T_A \leq +100^\circ\text{C}$. NOTE: No heat sink or forced air cooling on the devices shall be permitted.

4.4 Conformance inspection. Conformance inspection shall be in accordance with [MIL-PRF-19500](#), and as specified herein.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table E-V of [MIL-PRF-19500](#) and [table I](#) herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the tests and conditions specified for subgroup testing in table E-VIB (JAN, JANTX, and JANTXV) of [MIL-PRF-19500](#) and as follows. Delta requirements shall be in accordance with the applicable step of [4.6](#) herein.

4.4.2.1 Quality levels JAN, JANTX and JANTXV, table E-VIB of [MIL-PRF-19500](#).

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
B3	1037	$V_{CB} \geq 10 \text{ V dc}$; $\Delta T_J = \text{between cycles} \geq +100^\circ\text{C}$. $t_{on} = t_{off} = 3 \text{ minutes}$. No heat sink or forced-air cooling on the devices shall be permitted.
B5	3131	See 4.3.1 , $R_{\theta JC} = 1^\circ\text{C/W}$ (maximum).

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of [MIL-PRF-19500](#) and as follows. Delta requirements shall be in accordance with the applicable step of [4.6](#) herein.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
C2	2036	Test condition A, weight = 10 lbs (4.54 Kg), $t = 15\text{s}$.
C6	1037	$V_{CB} \geq 10 \text{ V dc}$; $\Delta T_J \text{ between cycles} \geq +100^\circ\text{C}$; $t_{on} = t_{off} = 3 \text{ minutes}$. No heat sink or forced-air cooling on device shall be permitted.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-IX of [MIL-PRF-19500](#) and as specified in [table II](#) herein. Delta requirements shall be in accordance with the applicable step of [4.6](#) herein.

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4.5 Method of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse response measurements. The conditions for pulse response measurement shall be as specified in section 4 of [MIL-STD-750](#).

4.6 Delta measurements. The requirements for delta measurements for groups B, C, and E inspection shall be as specified below. (1) (2) (3)

Step	Inspection	MIL-STD-750		Symbol	Limit
		Method	Conditions		
1	Forward-current transfer ratio	3076	$V_{CE} = 3 \text{ V dc}; I_C = 6.0 \text{ A dc};$ pulsed (see 4.5.1).	Δh_{FE2}	± 40 percent change from initial reading.

- (1) The delta measurement for group B, quality levels (JAN, JANTX and JANTXV) shall be as follows: In addition to the measurements specified for subgroups 3 and 6 of table E-VIB of [MIL-PRF-19500](#), the measurements of step 1 shall also be taken.
- (2) The delta measurement for group C shall be as follows: In addition to the measurements specified for subgroup 6 of table E-VII of [MIL-PRF-19500](#), the measurements of step 1 shall also be taken.
- (3) The delta measurement for group E shall be as follows: In addition to the measurements specified for subgroups 1 and 2 of table E-IX of [MIL-PRF-19500](#), the measurements of step 1 shall also be taken.

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TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>2/</u>	3131	See 4.3.1	$Z_{\theta JC}$			$^{\circ}C/W$
Collector to emitter breakdown voltage 2N6058 2N6059	3011	Bias condition D, $I_C = 100$ mA dc; pulsed (see 4.5.1)	$V_{(BR)CEO}$	80 100		V dc V dc
* Collector to emitter cutoff current 2N6058	3041	Bias condition A, $V_{BE} = 1.5$ V dc	I_{CEX1}		10	μA dc
* 2N6059		$V_{CE} = 80$ V dc $V_{CE} = 100$ V dc			10	μA dc
Collector to emitter cutoff current 2N6058 2N6059	3041	Bias condition D $V_{CE} = 40$ V dc $V_{CE} = 50$ V dc	I_{CEO}		1.0 1.0	mA dc mA dc
Emitter to base cutoff current	3061	Bias condition D, $V_{EB} = 5$ V dc	I_{EBO}		2.0	mA dc
Base to emitter voltage (nonsaturated)	3066	Test condition B, $V_{CE} = 3$ V dc; $I_C = 6$ A dc	V_{BE}		2.8	V dc
Base to emitter voltage (saturated)	3066	Test condition A, $I_C = 12$ A dc; $I_B = 120$ mA dc; pulsed (see 4.5.1)	$V_{BE(sat)}$		4.0	V dc
Collector to emitter voltage (saturation voltage)	3071	$I_C = 12$ A dc; $I_B = 120$ mA dc; pulsed (see 4.5.1)	$V_{CE(sat)1}$		3.0	V dc
Collector to emitter voltage (saturation voltage)	3071	$I_C = 6$ A dc; $I_B = 24$ mA dc; pulsed (see 4.5.1)	$V_{CE(sat)2}$		2.0	V dc
Forward-current transfer ratio	3076	$V_{CE} = 3$ V dc; $I_C = 1$ A dc; pulsed (see 4.5.1)	h_{FE1}	1,000		
Forward-current transfer ratio	3076	$V_{CE} = 3$ V dc; $I_C = 6$ A dc; pulsed (see 4.5.1)	h_{FE2}	1,000	18,000	
Forward-current transfer ratio	3076	$V_{CE} = 3$ V dc; $I_C = 12$ A dc; pulsed (see 4.5.1)	h_{FE3}	150		

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 3</u>		$T_A = +150^\circ\text{C}$				
High temperature operation:						
Collector to emitter cutoff current 2N6058 2N6059	3041	Bias condition A, $V_{BE} = 1.5\text{ V dc}$ $V_{CE} = 80\text{ V dc}$ $V_{CE} = 100\text{ V dc}$	I_{CEX2}		5.0 5.0	mA dc mA dc
Collector to emitter voltage (saturation voltage)	3071	$I_C = 6\text{ A dc}$; $I_B = 24\text{ mA dc}$; pulsed (see 4.5.1)	$V_{CE(sat)3}$		2.0	V dc
Low temperature operation:		$T_A = -55^\circ\text{C}$				
Forward-current transfer ratio	3076	$V_{CE} = 3\text{ V dc}$; $I_C = 6\text{ A dc}$; pulsed (see 4.5.1)	h_{FE4}	300		
<u>Subgroup 4</u>						
Small-signal, short-circuit forward-current transfer ratio	3206	$V_{CE} = 3\text{ V dc}$; $I_C = 5\text{ A dc}$; $f = 1\text{ kHz}$	h_{fe}	1,000		
Magnitude of common-emitter small-signal short-circuit forward-current transfer ratio	3306	$V_{CE} = 3\text{ V dc}$; $I_C = 5\text{ A dc}$; $f = 1.0\text{ MHz}$	$ h_{fe} $	10	250	
Open-circuit output capacitance	3236	$V_{CB} = 10\text{ V dc}$; $I_E = 0$; $100\text{ kHz} \leq f \leq 1\text{ MHz}$	C_{obo}		300	pF
Pulse response						
Turn-on time		(See figure 2), $V_{CC} = 30\text{ V dc}$; $I_C = 5\text{ A dc}$; $I_B = 20\text{ mA dc}$	t_{on}		2.0	μs
Turn-off time		(See figure 2); $V_{CC} = 30\text{ V dc}$; $I_C = 5\text{ A dc}$; $I_{B1} = I_{B2} = 20\text{ mA dc}$	t_{off}		10	μs

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection ^{1/}	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 5</u>						
Safe operating area (continuous dc)	3051	$T_C = +25^\circ\text{C} +10^\circ\text{C}, -0^\circ$; $t \geq 1 \text{ s}$; 1 cycle; (see figure 3)				
<u>Test 1</u> (Both device types)		$V_{CE} = 12.5 \text{ V dc}$; $I_C = 12 \text{ A dc}$				
<u>Test 2</u> (Both device types)		$V_{CE} = 30 \text{ V dc}$; $I_C = 5 \text{ A dc}$				
<u>Test 3</u> (2N6058) (2N6059)		$V_{CE} = 70 \text{ V dc}$; $I_C = 200 \text{ mA dc}$ $V_{CE} = 90 \text{ V dc}$; $I_C = 155 \text{ mA dc}$				
Safe operating area (switching)	3053	Load condition C; (unclamped inductive load); $T_A = +25^\circ\text{C}$; $t_r + t_f \leq 1.0 \mu\text{s}$; duty cycle ≤ 2 percent; $t_p = 1 \text{ ms}$; (vary to obtain I_C); $R_s = 0.10 \Omega$; $R_{BB1} = 80 \Omega$; $V_{BB1} = 16 \text{ V dc}$; $R_{BB2} = 100 \Omega$; $V_{BB2} = 1.5 \text{ V dc}$; $I_C = 12 \text{ A dc}$; $V_{CC} = 20 \text{ V dc}$; $R_L \leq 2 \Omega$; $L = 10 \text{ mH}$ (Stancor C-2688 or equivalent); (see figure 4).				
2N6058 2N6059		Clamp voltage = $80 +0, -5 \text{ V dc}$ Clamp voltage = $100 +0, -5 \text{ V dc}$				
		Device fails if clamp voltage not reached.				
End-point electrical measurements		See subgroup 2 of table I herein.				
<u>Subgroups 6 and 7</u>						
Not applicable						

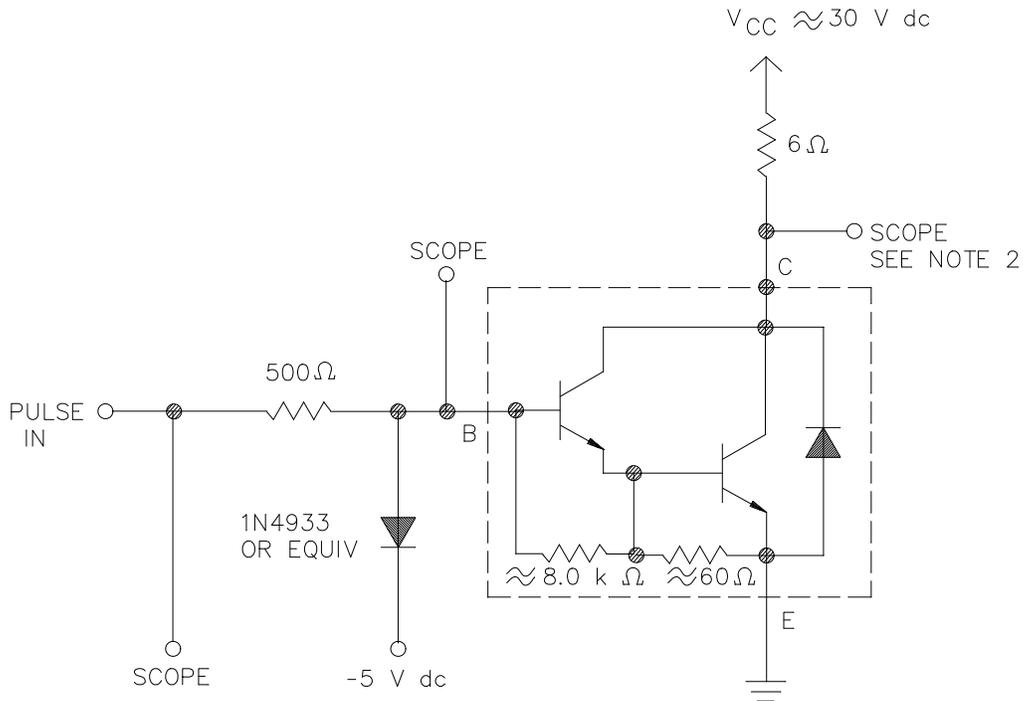
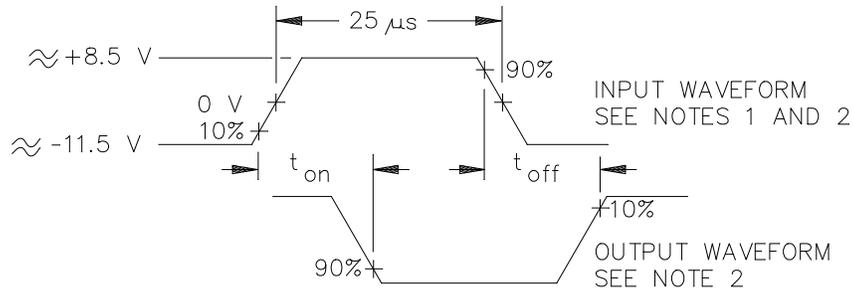
^{1/} For sampling plan, see [MIL-PRF-19500](#).^{2/} This test required for the following end-point measurements only:
Group B, subgroups 2 and 3 (JAN, JANTX, and JANTXV).
Group C, subgroup 2 and 6.
Group E, subgroup 1.

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TABLE II. Group E inspection (all quality levels) - for qualification and requalification only.

Inspection	MIL-STD-750		Sample plan
	Method	Conditions	
<u>Subgroup 1</u>			45 devices c = 0
Temperature cycling (air to air)	1051	Test condition C, 500 cycles.	
Hermetic seal Fine leak Gross leak	1071		
End-point electrical measurements		See table I , subgroup 2 and 4.6 herein.	
<u>Subgroup 2</u>			45 devices c = 0
Intermittent operation life	1037	$V_{CB} \geq 10$ V dc, 6,000 cycles.	
End-point electrical measurements		See table I , subgroup 2 and 4.6 herein.	
<u>Subgroup 4</u>			Sample size N/A
Thermal impedance curves		See MIL-PRF-19500 .	
<u>Subgroup 8</u>			45 devices c = 0
Reverse voltage leakage stability	1033	Condition B.	

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NOTES:

1. The input waveform is supplied by a pulse generator with the following characteristics:
 $t_r \leq 20 \text{ ns}$, $t_f \leq 20 \text{ ns}$, $Z_{\text{OUT}} = 50 \text{ ohms}$, $\text{PW} = 25 \mu\text{s}$, duty cycle ≤ 2 percent.
2. Output waveforms are monitored on an oscilloscope with the following characteristics:
 $t_r \leq 2.0 \text{ ns}$, $Z_{\text{in}} \geq 20 \text{ k}\Omega$, $C_{\text{in}} \leq 11.5 \text{ pf}$.
3. Resistors shall be non-inductive types.
4. The dc power supplies may require additional by-passing in order to minimize ringing.

FIGURE 2. Pulse response test circuit.

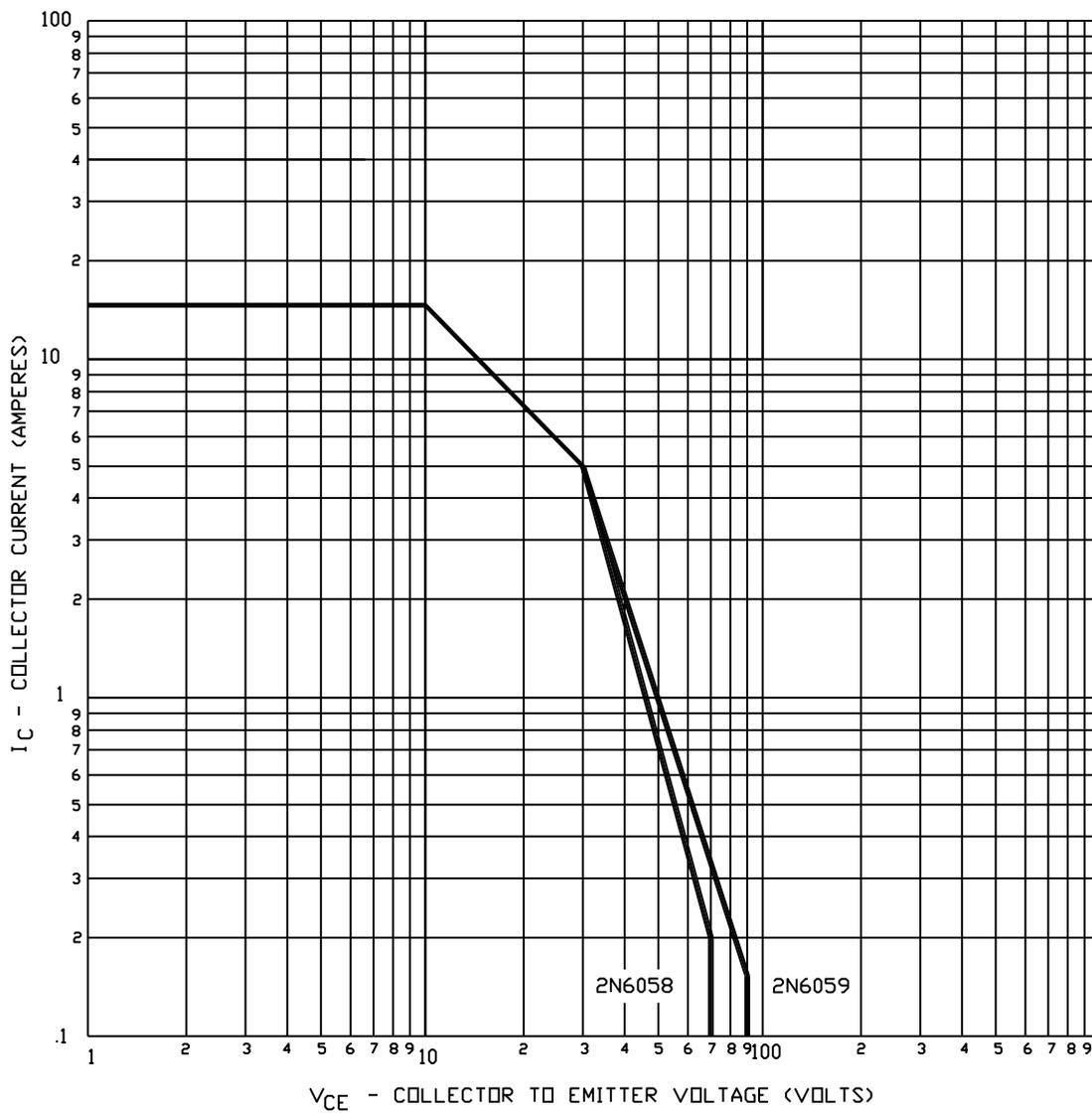


FIGURE 3. Maximum safe operating area graph (continuous dc).

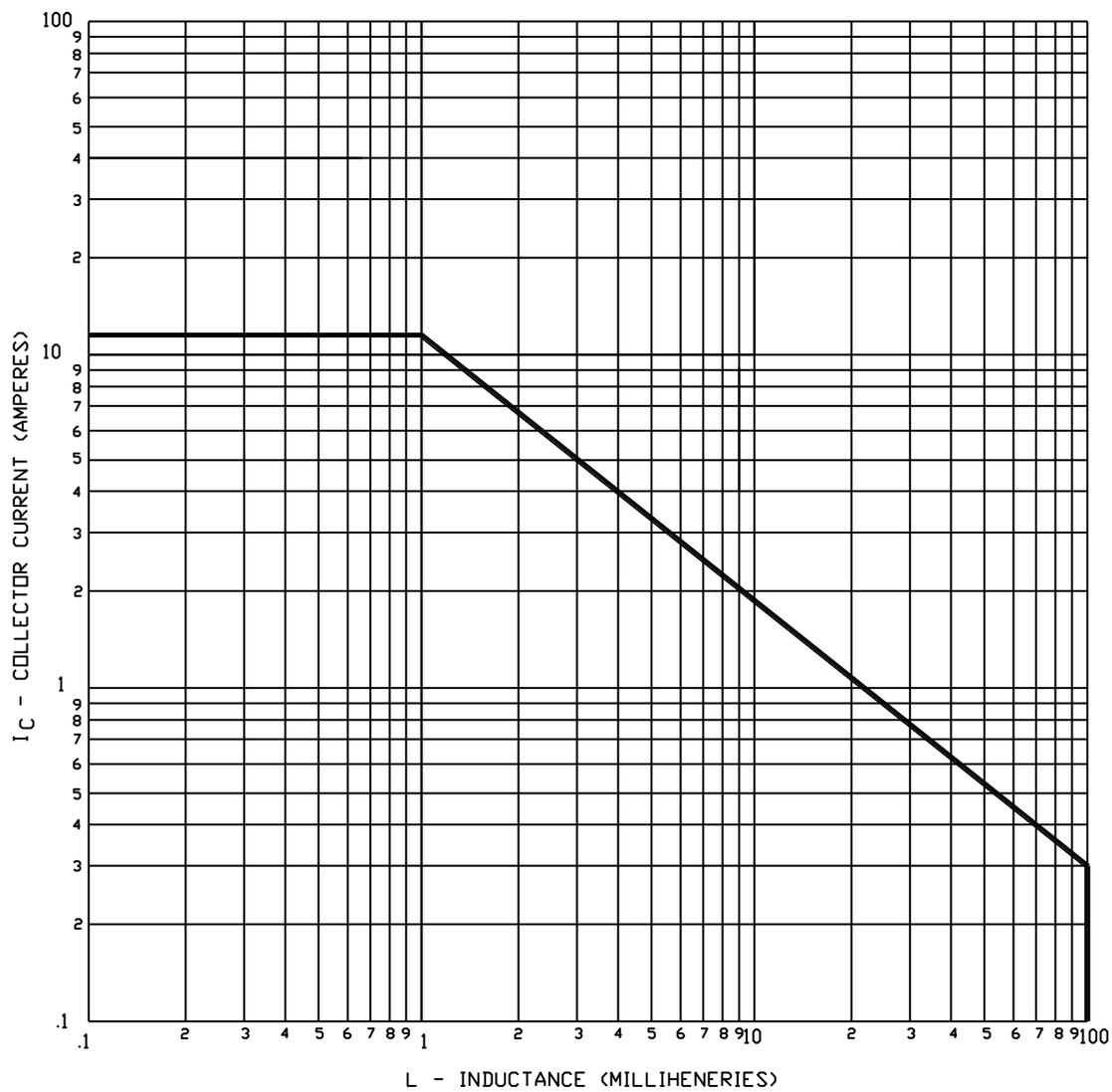


FIGURE 4. Safe operating area for switching between saturation and cutoff (unclamped inductive load).

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.) The notes specified in [MIL-PRF-19500](#) are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

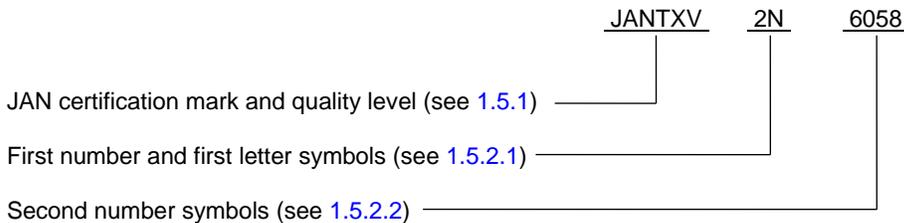
6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see [3.4.1](#)).
- d. The complete PIN, see [1.5](#) and [6.5](#).

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime, ATTN: VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil. An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.dla.mil>.

6.4 PIN construction example.

6.4.1 Encapsulated devices The PINs for encapsulated devices are constructed using the following form.



6.5 List of PINs.

6.5.1 List of PINs for encapsulated devices. The following is a list of possible PINs for encapsulated devices available on this specification sheet.

PINs for devices of the base quality level	PINs for devices of the "TX" quality level	PINs for devices of the "TXV" quality level
JAN2N6058	JANTX2N6058	JANTXV2N6058
JAN2N6059	JANTX2N6059	JANTXV2N6059

6.6 Request for new types and configurations. Requests for new device types or configurations for inclusions in this specification sheet should be submitted to: DLA Land and Maritime, ATTN: VAC, Post Office Box 3990, Columbus, OH 43218-3990 or by electronic mail at Semiconductor@dla.mil or by facsimile (614) 693-1642 or DSN 850-6939.

6.7 Changes from previous issue. Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extent of the changes.

Custodians:
 Army - CR
 Navy - EC
 Air Force - 85
 NASA - NA
 DLA - CC

Preparing activity:
 DLA - CC
 (Project 5961-2016-026)

Review activities:
 Air Force - 19, 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil>.